

Technology and Manufacturing: an Intel Advantage

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Today's presentation contains forward-looking statements. All statements made that are not historical facts are subject to a number of risks and uncertainties, and actual results may differ materially. Please refer to our most recent Earnings Release and our most recent Form 10-Q or 10-K filing for more information on the risk factors that could cause actual results to differ.

Our Core Assets Are
Increasingly Valuable

- ✓ *Silicon Process Technology*
- ✓ *Intel Architecture based Platforms*
- ✓ *Market Creation*
(Capacity, Scale, Diffusion)



Technology and Manufacturing: An Intel Advantage

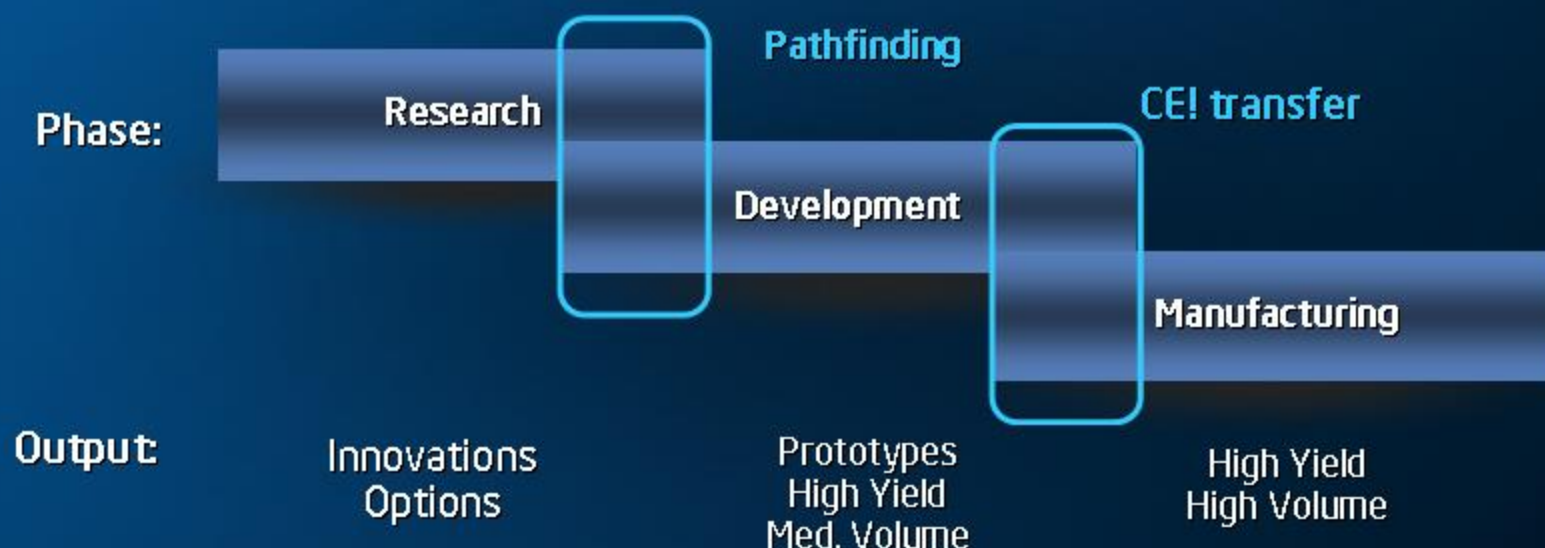
- Technology innovation is the driver
- 65nm and manufacturing excellence
- 45nm and industry leadership

We Have a Well-Honed, *Unique* R-D-M Method

Traditional R-D-M Method:



Intel's R-D-M Method:



R&D System Delivers World-Class Results

1997

1999

2001

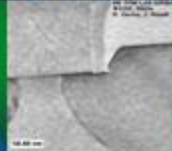
2003

2005

2007

Forecast

Strained silicon



Development
'01-'02



Production '03



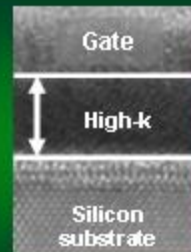
Production '05

High-k metal gate

Research: Materials
& ALD '96 - '99

Materials
selected
2000

Metal gates
research
2001



Demonstrated '03

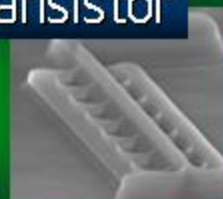
Development
'05-'06



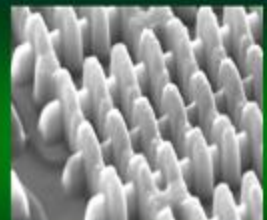
Prod. '07

Tri-gate transistor

Research



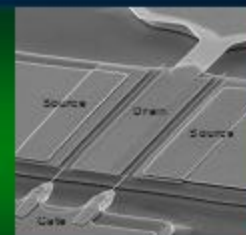
Demonstrated '02



Strain+ high k+ tri-gate '06

III-V

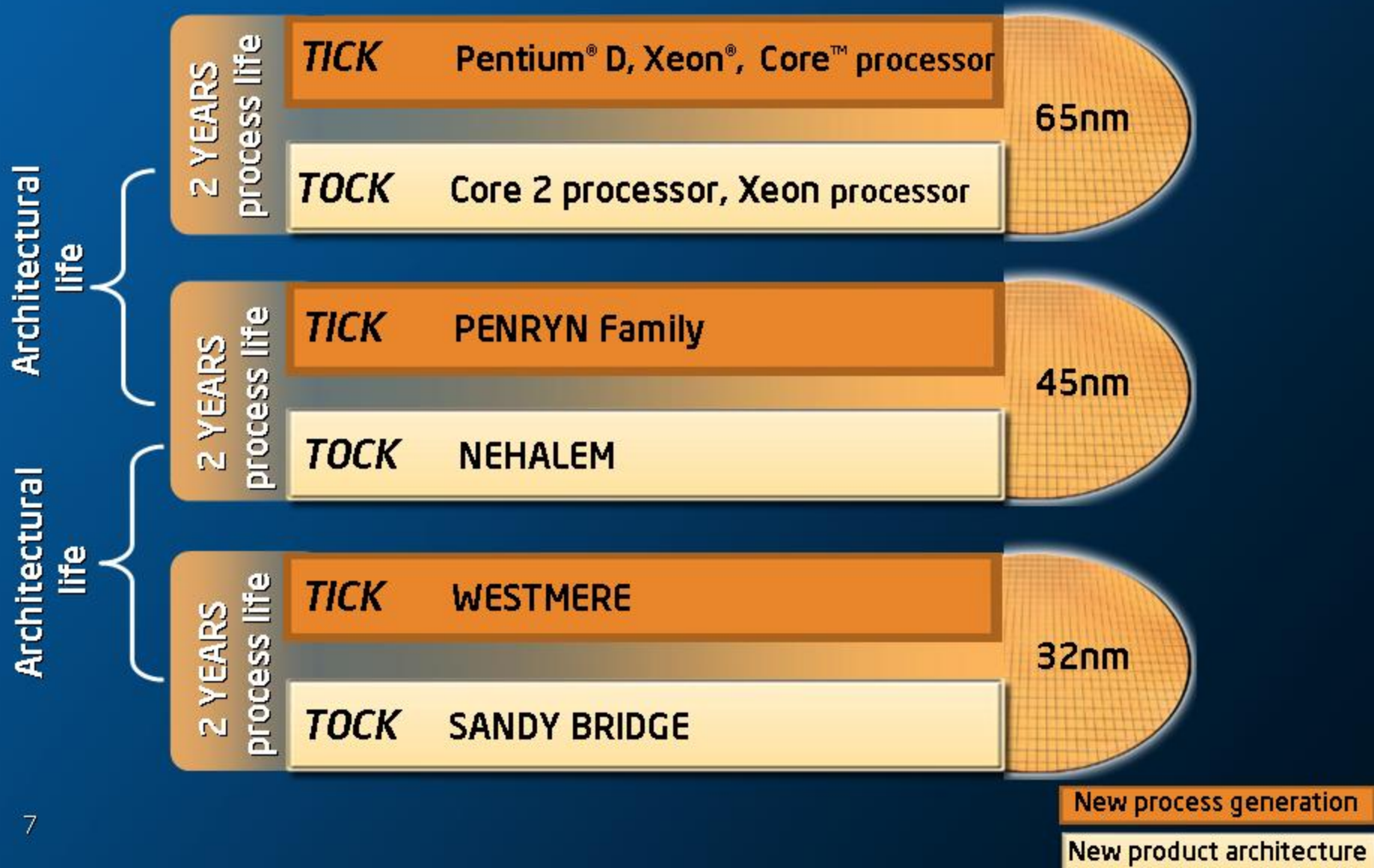
Collaborative
Research



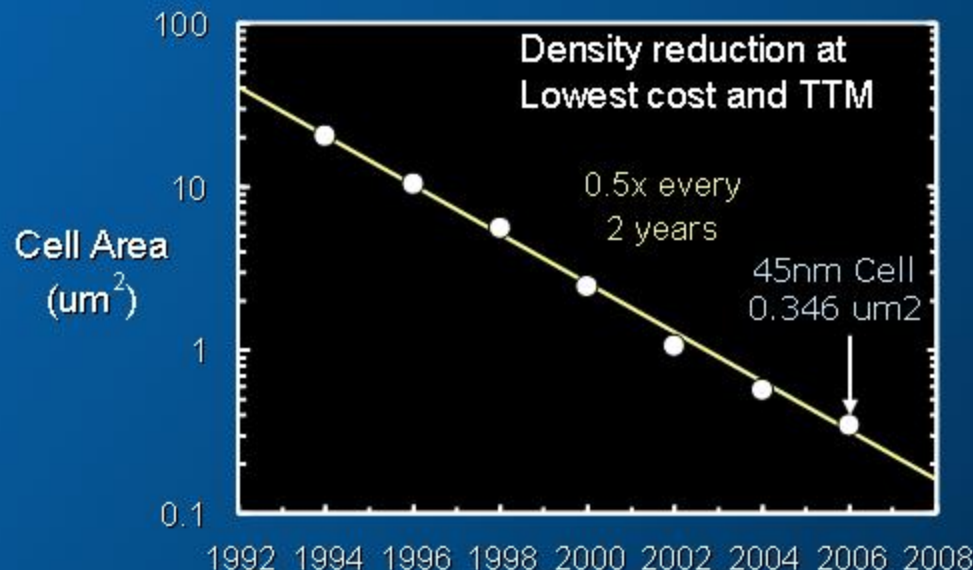
Demonstrated 2005

... and the pipeline is full

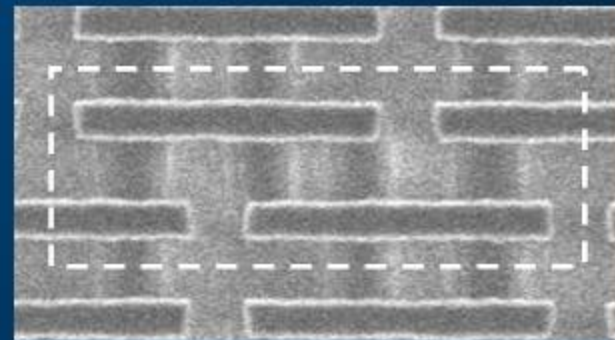
Alternating Process and Product Introductions for Sustained Leadership



Development with a Cost Focus: Dry 193 lithography for 45nm

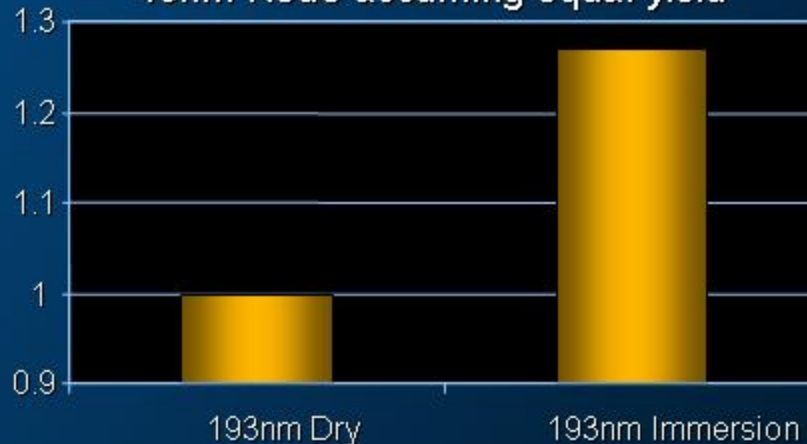


SRAM - Functional silicon in Jan '06

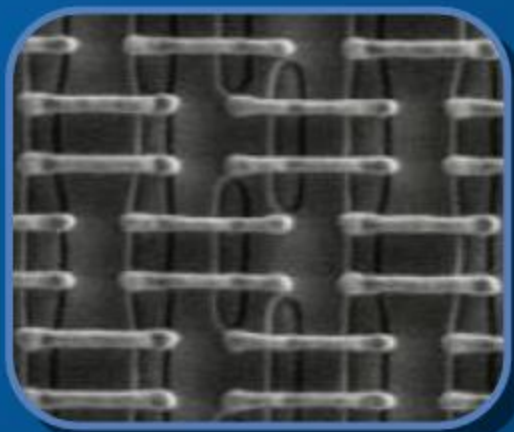


Exceptional Gate control enabled by Intel's DFM (design for manufacturability)

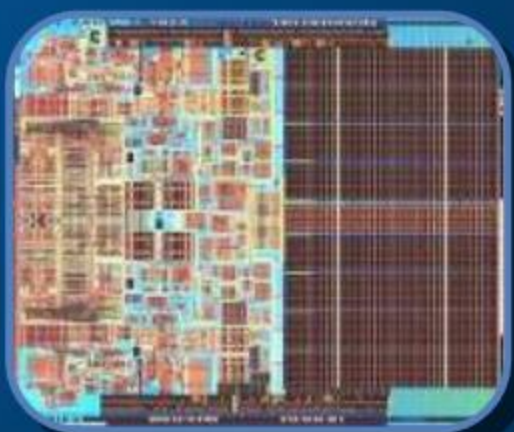
Critical Layer Lithography Cost Comparison
45nm Node assuming equal yield



Complete Internal Capabilities Enable Practical DFM that delivers real benefits



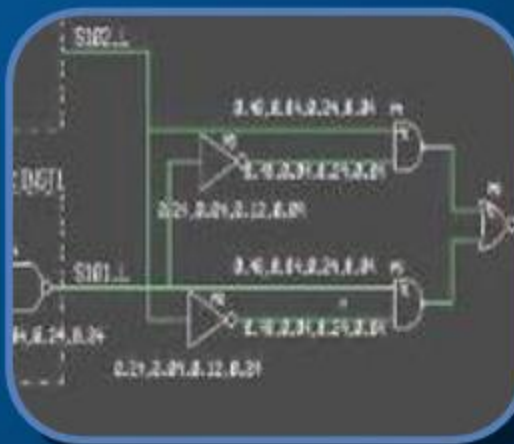
Process



Product



Leading-edge Capacity



Design Tools



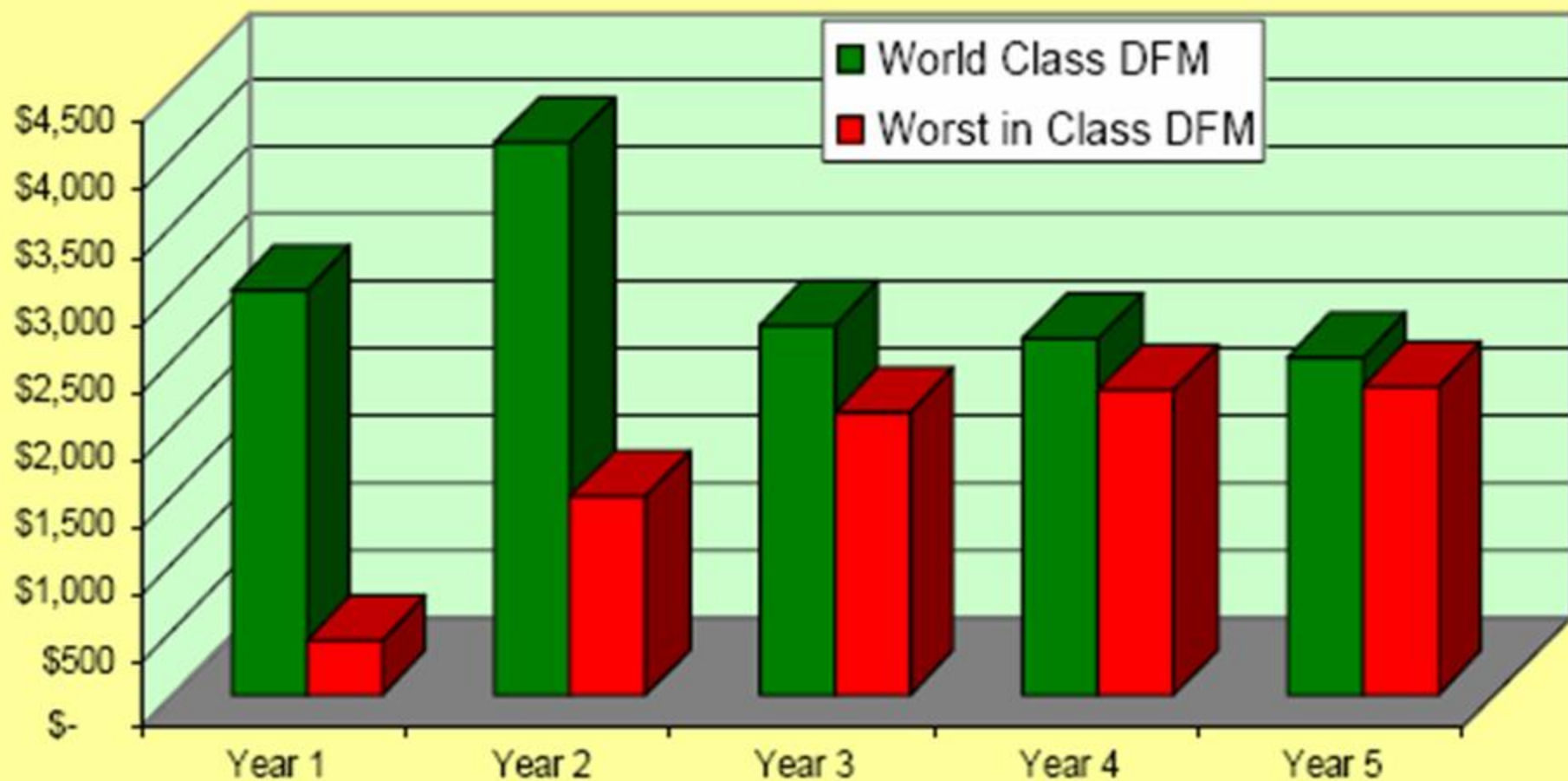
Masks



Packaging

How DFM Can Affect Annual Revenue

(from a 300mm fab in \$M)

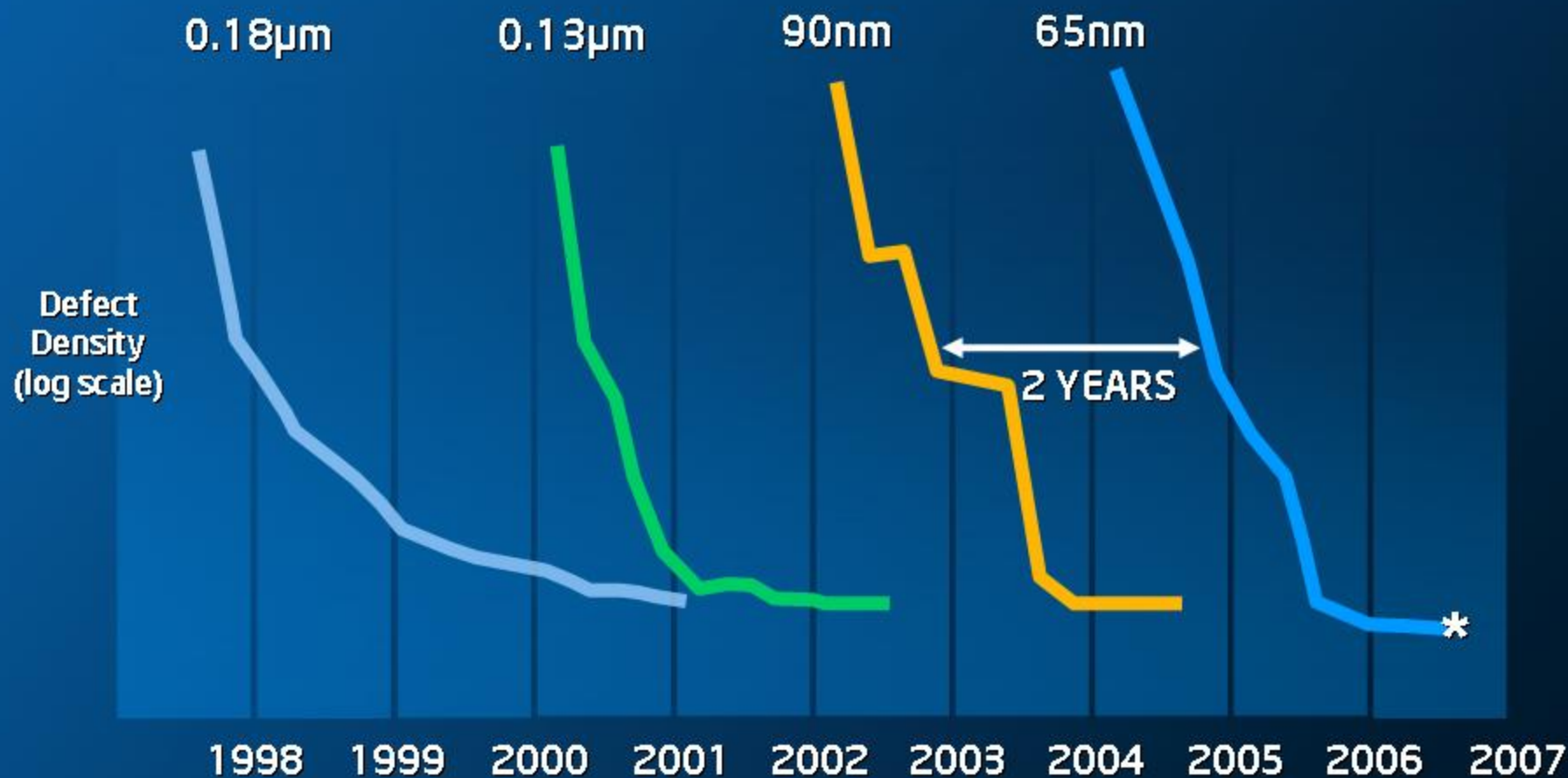


Source: VLSI Research, January '07
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Technology and Manufacturing: An Intel Advantage

- Technology innovation is the driver
- 65nm and manufacturing excellence
 - Leading on Multiple measures
- 45nm and industry leadership

Yields are a Key Measure of Manufacturing Excellence

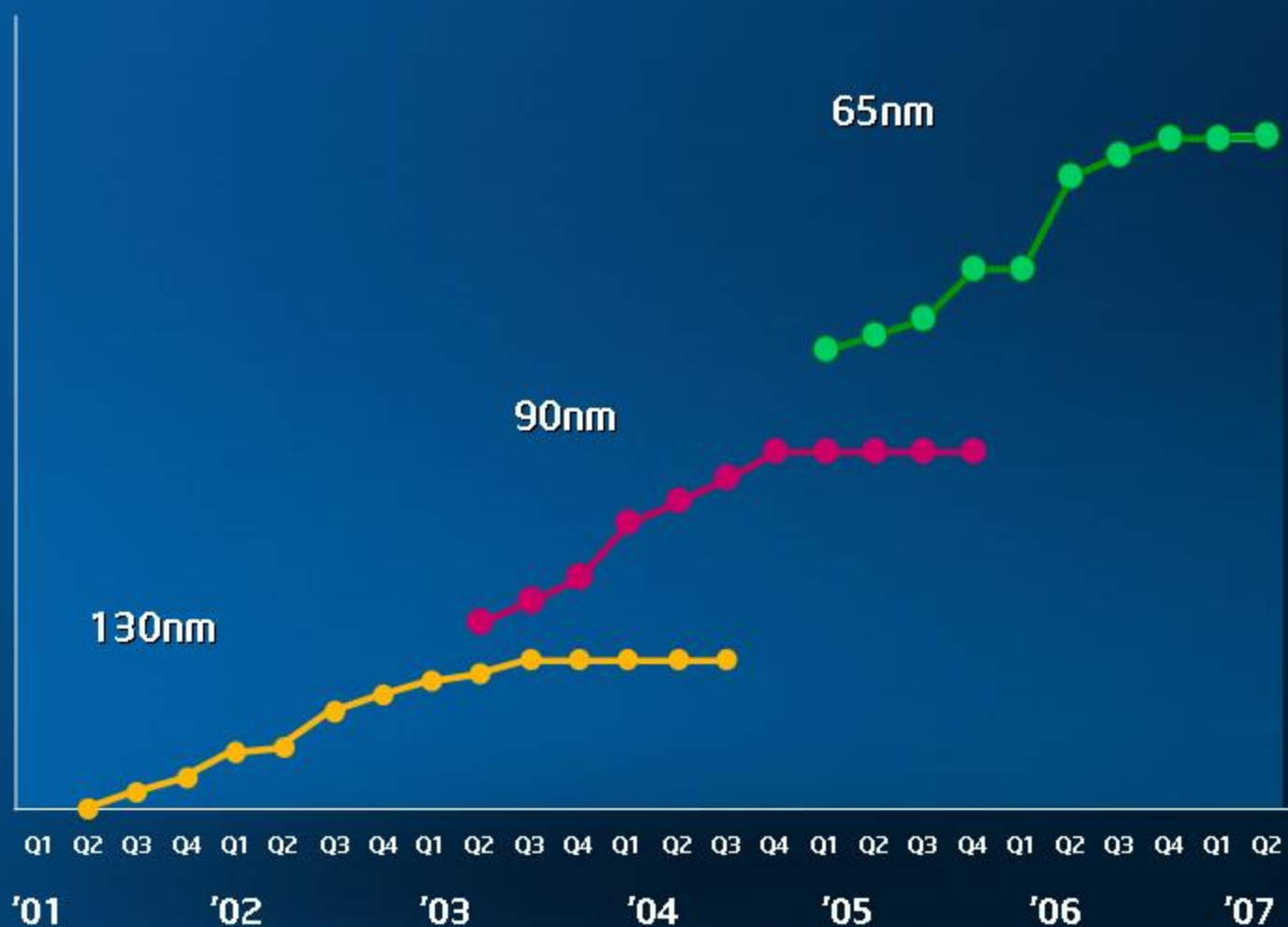


R-D-M Pipeline Benefit - better yields, faster ramps, lower costs

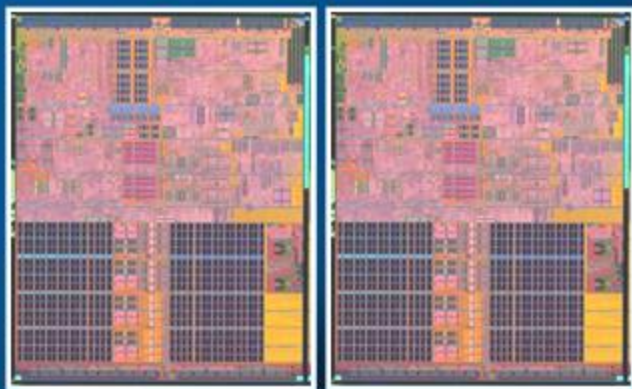
* 65nm CPU Shipment Crossover

Continuous Improvement Is Nothing New

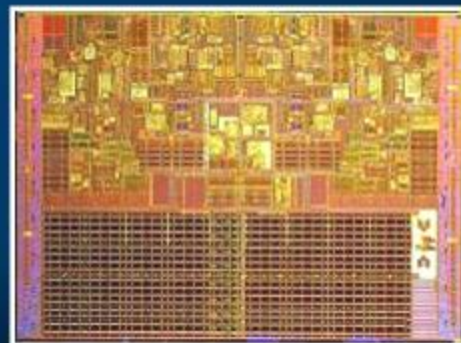
Normalized Transistor Performance



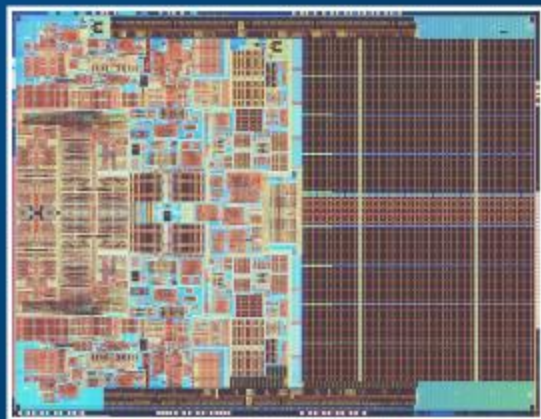
120M 65 nm CPUs Shipped through April '07



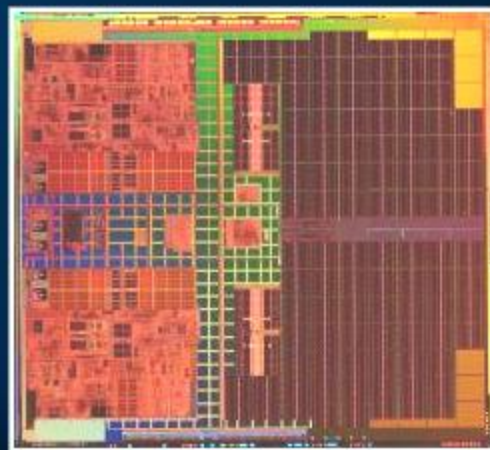
Intel Pentium® D Processor
Q4'05



Intel Core™ Duo Processor
Q4'05



Intel Core™2 Duo Processor
Q2'06



Intel Dual-Core Xeon® 7100
Processor, Q3'06

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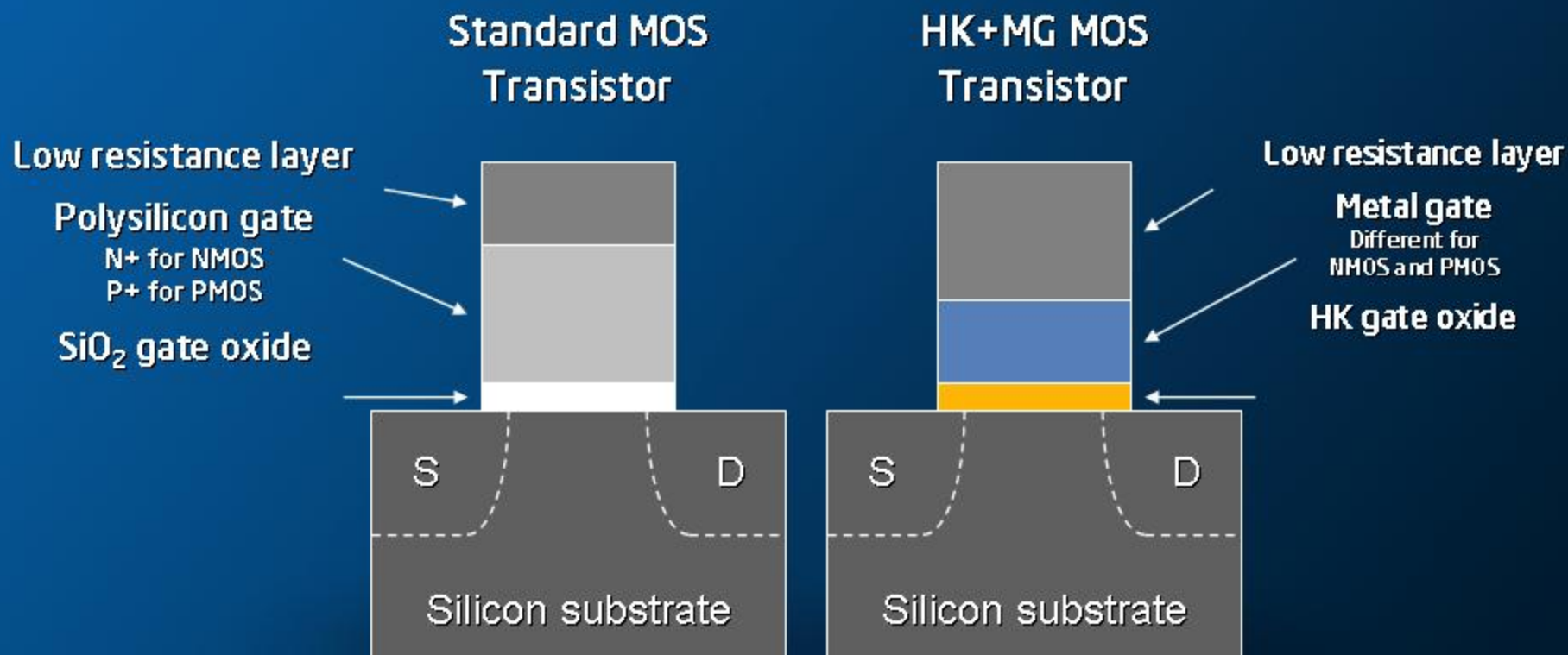
- Technology innovation is the driver
- 65nm and manufacturing excellence
- 45nm and industry leadership
 - Optimized for performance and cost

Extending the Lead at 45nm Technology with High-k/ Metal Gate Transistors

- ~2x improvement in transistor density –
for either smaller chip size or increased transistor count
- >20% improvement in transistor switching speed
or
- >5x reduction in source-drain leakage power
- >10x reduction in gate oxide leakage power
- >30% reduction in transistor switching power

Benefits of Intel's 45nm technology compared to 65 nm technology

High-k + Metal Gate: The Biggest Change in Transistors in 40 Years



High-k + metal gate enables continuation of transistor scaling

High-k + Metal Gate Delivers True Performance per Watt Improvement

#1: Power Reduction

(energy efficient computing)

1/10th gate oxide leakage

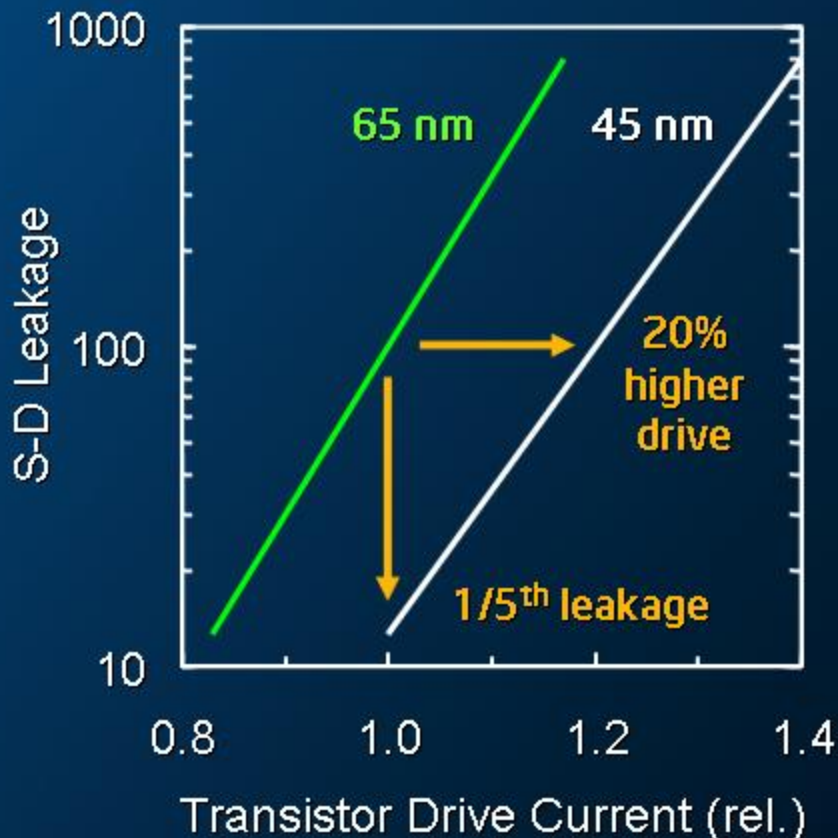
1/5th S-D leakage

#2: Performance Increase

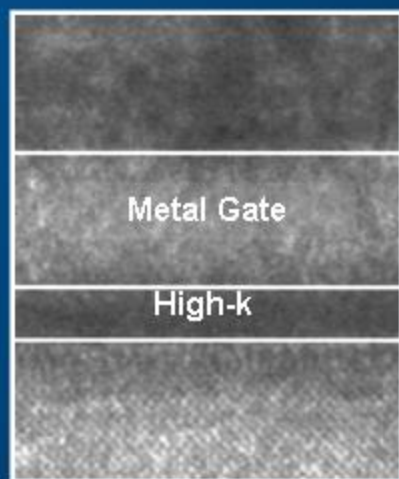
20% higher drive current

#3: Scaling

Higher drive allows scaled transistor width

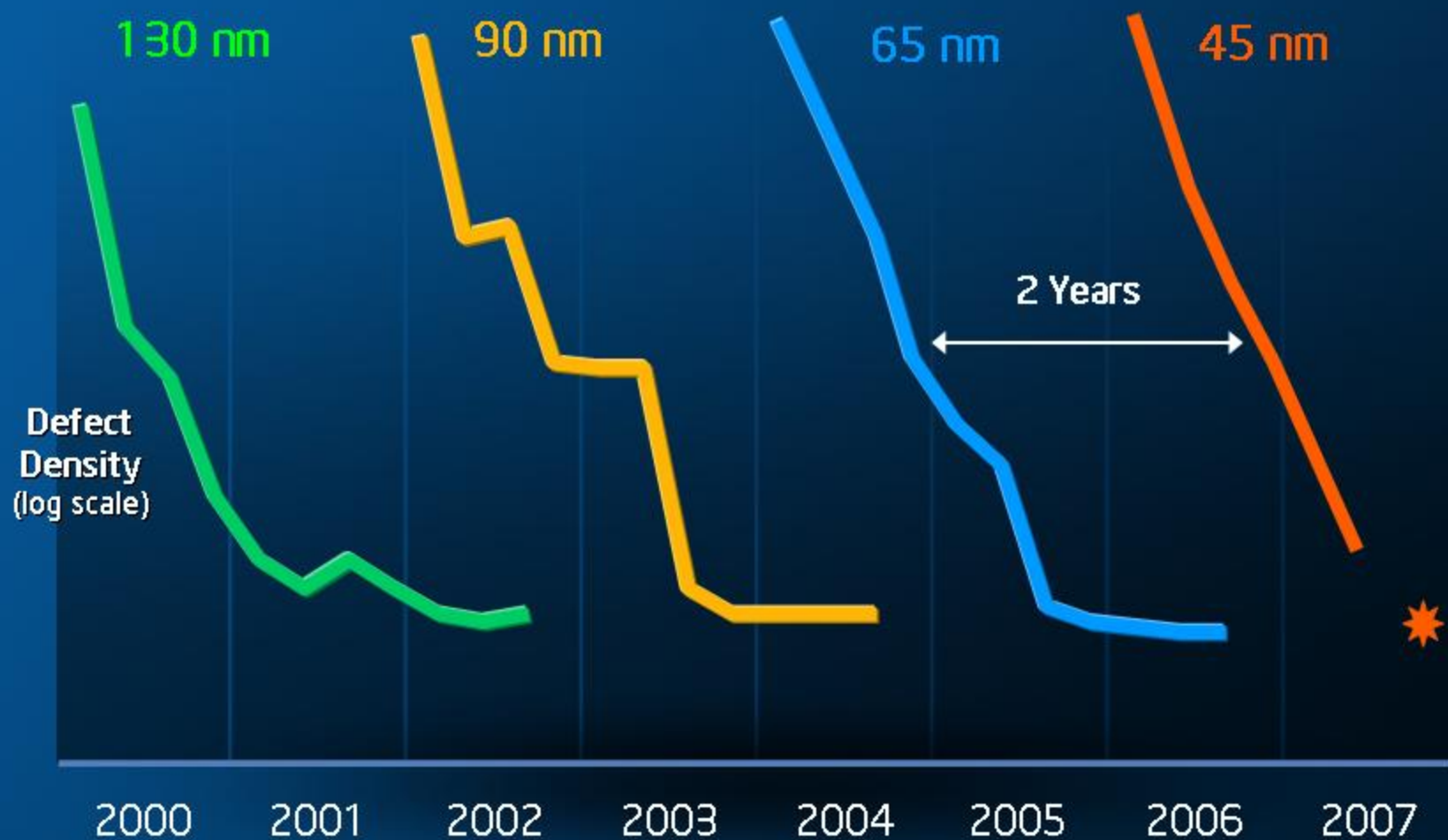


... And a Bargain at That



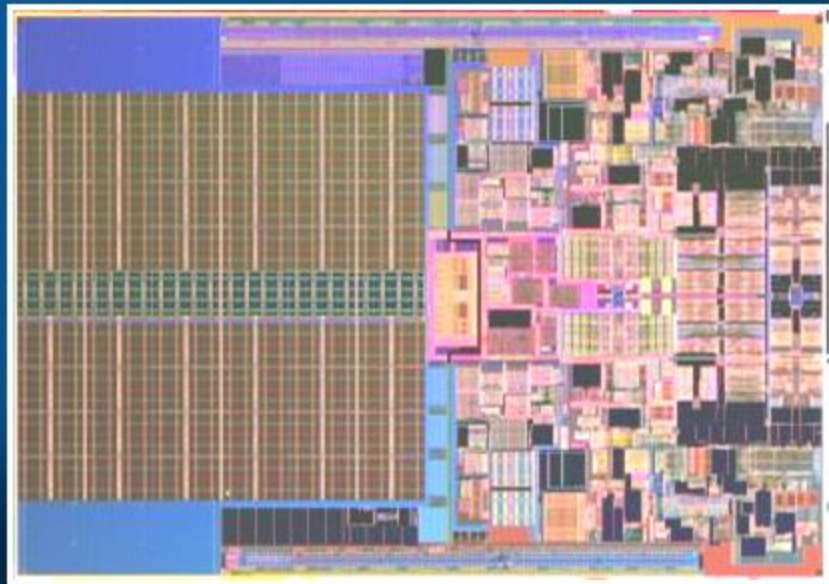
- HK+MG adds $\sim 4\%$ to processed wafer cost
- About same cost as a metal + via layer
- Less than $1/3$ the cost adder of SOI wafers

Yield on Track for 45nm Production



Source: Intel Internal

World's First Working 45 nm CPUs



Penryn

45 nm Intel® Core™2
family processor

*Mobile, desktop, workstation,
and server applications*



Silverthorne

45 nm Intel Ultra Low Power
Processors

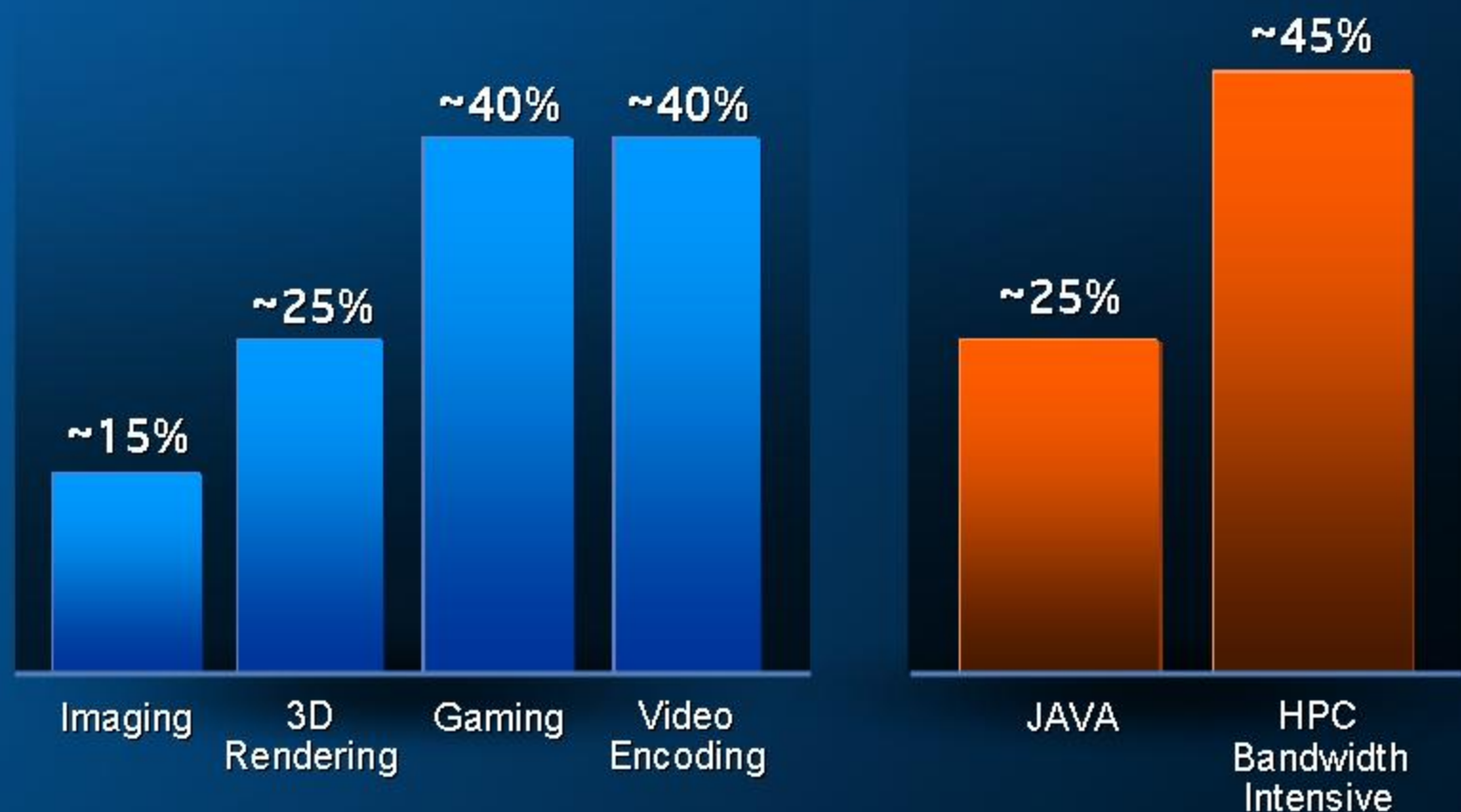
*For mobile internet devices
and ultra mobile PCs*

Early Penryn Family Performance Indicators

45nm High-k vs. 65nm Intel® Core™ 2 and Xeon™ Processors

CLIENT (Quad Core)

SERVER (Quad Core)



Source: Intel

Impact of Silverthorne on Power and Size

CPU + CHIPSET



Source: Intel Forecast

Projected CPU Shipments



Source: Intel Internal

Technology and Manufacturing: An Intel Advantage

- Technology innovation
 - Effective R & D pipeline delivers sustained results
- 65nm and manufacturing excellence
 - Leading on Multiple measures
- 45nm and industry leadership
 - Optimized for performance and cost

Thank You

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